EN: This Datasheet/Document is presented by the manufacturer.

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2SC1815

SILICON
NPN TRANSISTOR



TO-92 CASE

Central Semiconductor Corp.

www.centralsemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR 2SC1815 is a silicon NPN transistor, manufactured by the epitaxial planar process, designed for general purpose amplifier applications.

MARKING: FULL PART NUMBER

MAXIMUM RATINGS: (T_A=25°C unless otherwise noted)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	60	V
Collector-Emitter Voltage	V_{CEO}	50	V
Emitter-Base Voltage	V_{EBO}	5.0	V
Continuous Collector Current	I_C	150	mA
Power Dissipation	P_D	400	mW
Operating and Storage Junction Temperature	T_J, T_{stg}	-55 to +125	°C
Thermal Resistance	Θ_{JA}	250	°C/W

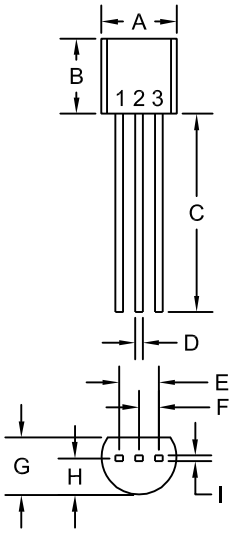
ELECTRICAL CHARACTERISTICS: (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	V_{CB}=60V		100	nA
I_{CEO}	V_{CE}=50V		100	nA
I_{EBO}	V_{EB}=5.0V		100	nA
BV_{CBO}	I_C=100μA	60		V
BV_{CEO}	I_C=100μA	50		V
BV_{EBO}	I_E=100μA	5.0		V
$V_{CE(SAT)}$	I_C=100mA, I_B=10mA		0.25	V
$V_{BE(SAT)}$	I_C=100mA, I_B=10mA		1.0	V
V_{BE}	I_E=310mA		1.45	V
h_{FE}	V_{CE}=6.0V, I_C=2.0mA	70	700	
f_t	V_{CE}=10V, I_C=1.0mA, f=30MHz	80		MHz

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TO-92 CASE - MECHANICAL OUTLINE



R1

DIMENSIONS				
	INCHES		MILLIMETERS	
SYMBOL	MIN	MAX	MIN	MAX
A (DIA)	0.175	0.205	4.45	5.21
B	0.170	0.210	4.32	5.33
C	0.500	-	12.70	-
D	0.016	0.022	0.41	0.56
E	0.100		2.54	
F	0.050		1.27	
G	0.125	0.165	3.18	4.19
H	0.080	0.105	2.03	2.67
I	0.015		0.38	

TO-92 (REV: R1)

LEAD CODE:
1) Emitter
2) Collector
3) Base

MARKING: FULL PART NUMBER